MOSFET – Single N-Channel, Small Signal, XLLGA3, 0.62 x 0.62 x 0.4

20 V, 224 mA

NTNS3193NZ

MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
20 V	1.4 Ω @ 4.5 V	224 mA
	1.9 Ω @ 2.5 V	
	2.2 Ω @ 1.8 V	
	4.3 Ω @ 1.5 V	

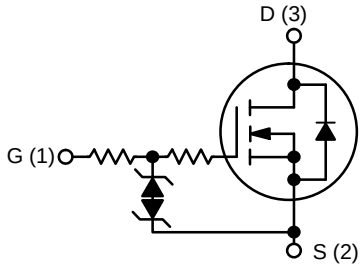
Features

- Single N-Channel MOSFET
- Ultra Small and Thin Package (0.62 x 0.62 x 0.4 mm)
- Low $R_{DS(on)}$ Solution in 0.62 x 0.62 mm Package
- 1.5 V Gate Voltage Rating
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

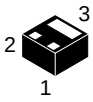
Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

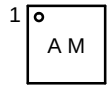
N-Channel MOSFET



MARKING DIAGRAM



XLLGA3
CASE 713AB



A = Specific Device Code
M = Date Code

MAXIMUM RATINGS (T_J = 25 °C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V_{DSS}	20	V
Gate-to-Source Voltage			V_{GS}	±8.0	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25 °C	I_D	224	mA
		T_A = 85 °C		162	
	t ≤ 5 s	T_A = 25 °C		241	
Power Dissipation (Note 1)	Steady State	T_A = 25 °C	P_D	120	mW
	t ≤ 5 s	T_A = 25 °C		139	
Pulsed Drain Current		t_p = 10 μs	I_{DM}	673	mA
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	120	mA
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	1040	°C/W
Junction-to-Ambient – t ≤ 5 s (Note 1)	$R_{\theta JA}$	900	

1. Surface Mounted on FR4 Board using the minimum recommended pad size, (or 2 mm^2), 1 oz Cu.
2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

ORDERING INFORMATION

Device	Package	Shipping†
NTNS3193NZT5G	XLLGA3 (Pb-Free)	8000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA	20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = −250 μA, ref to 25 °C		19		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 20 V; T_J = 25 °C			1.0	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8.0 V			±2.0	μA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA	0.4		1.0	V
Negative Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			1.9		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 100 mA		0.65	1.4	Ω
		V_{GS} = 2.5 V, I_D = 50 mA		0.9	1.9	
		V_{GS} = 1.8 V, I_D = 20 mA		1.1	2.2	
		V_{GS} = 1.5 V, I_D = 10 mA		1.4	4.3	
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = 100 mA		0.56		S
Source-Drain Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 10 mA		0.55	1.0	V
CHARGES & CAPACITANCES						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 15 V		15.8		pF
Output Capacitance	C_{OSS}			3.5		
Reverse Transfer Capacitance	C_{RSS}			2.4		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 200 mA		0.70		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.05		
Gate-to-Source Charge	Q_{GS}			0.14		
Gate-to-Drain Charge	Q_{GD}			0.10		
SWITCHING CHARACTERISTICS, VGS = 4.5 V (Note 3)						
Turn-On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DD} = 15 V, I_D = 200 mA, R_G = 2 Ω		18		ns
Rise Time	t_r			35		
Turn-Off Delay Time	$t_{d(OFF)}$			201		
Fall Time	t_f			110		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

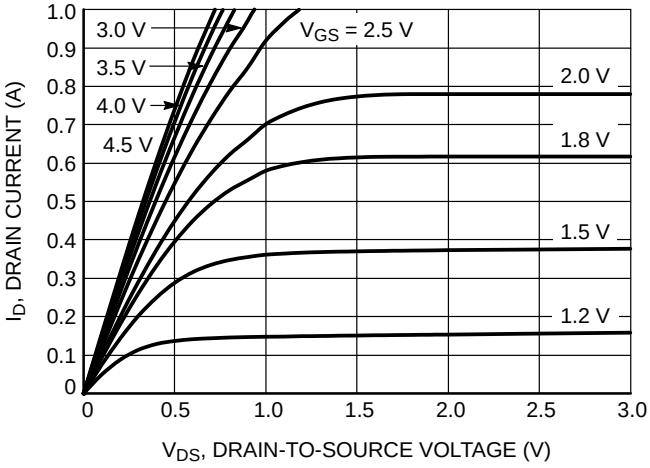


Figure 1. On-Region Characteristics

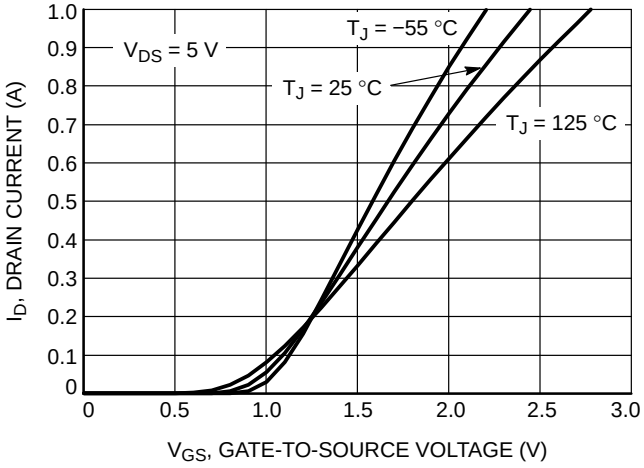


Figure 2. Transfer Characteristics

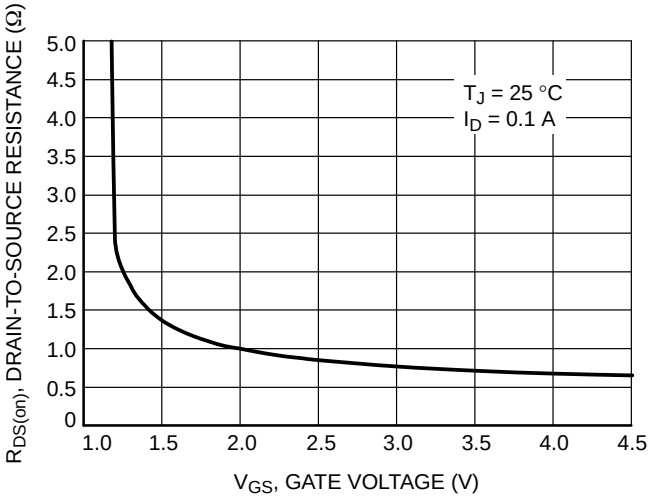


Figure 3. On-Resistance vs. Gate-to-Source Voltage

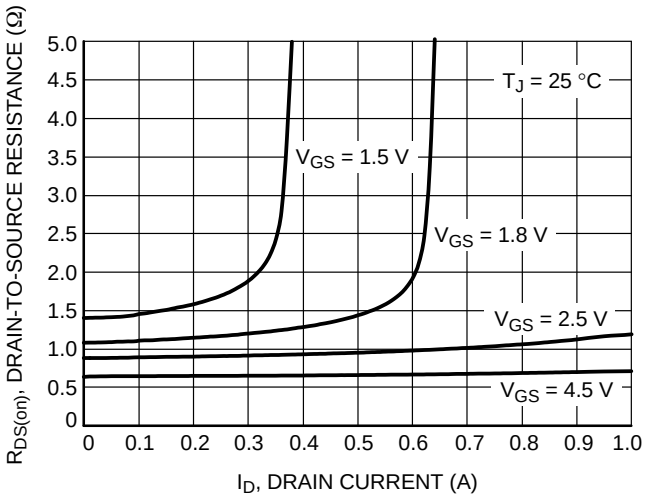


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

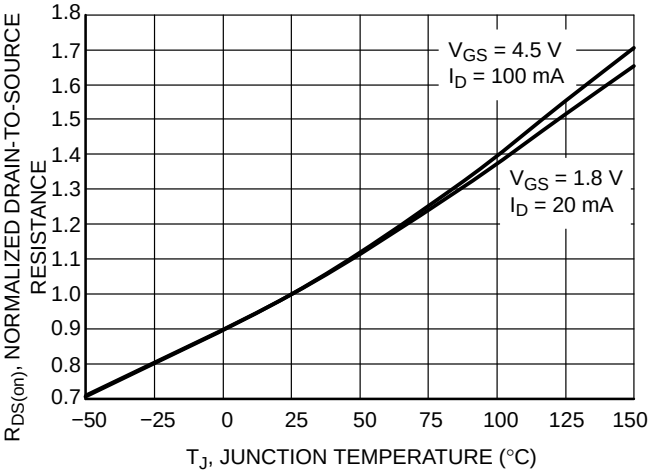


Figure 5. On-Resistance Variation with Temperature

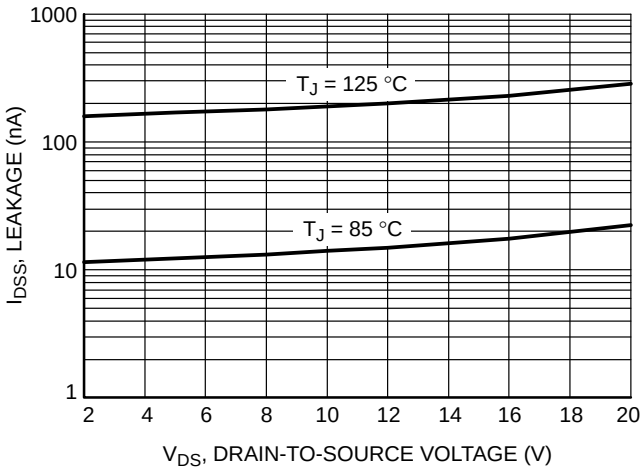


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

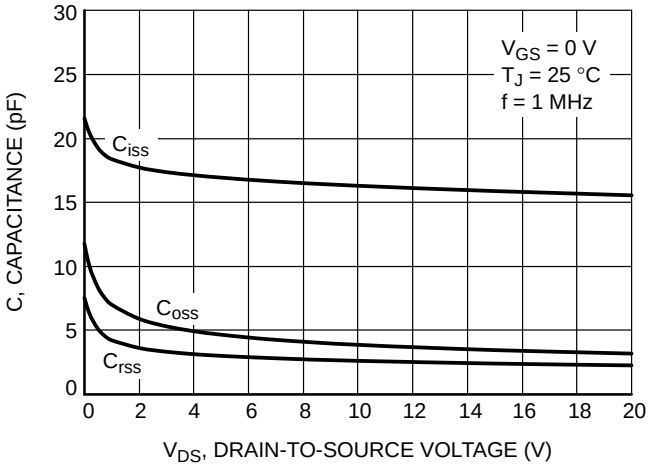


Figure 7. Capacitance Variation

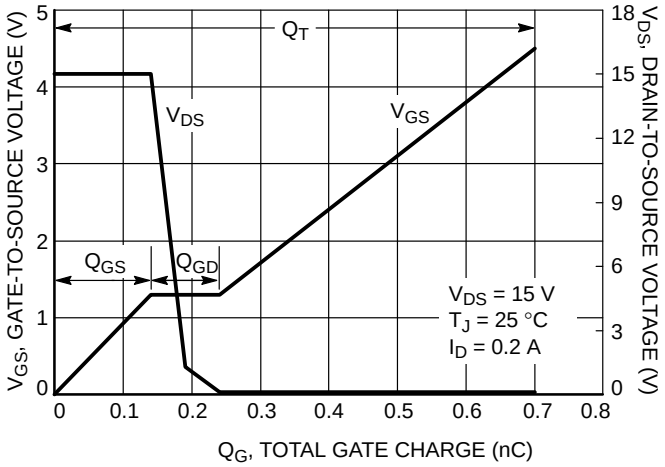


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

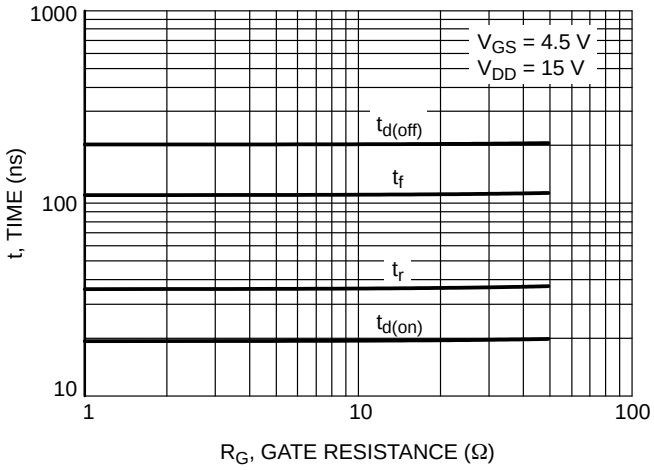


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

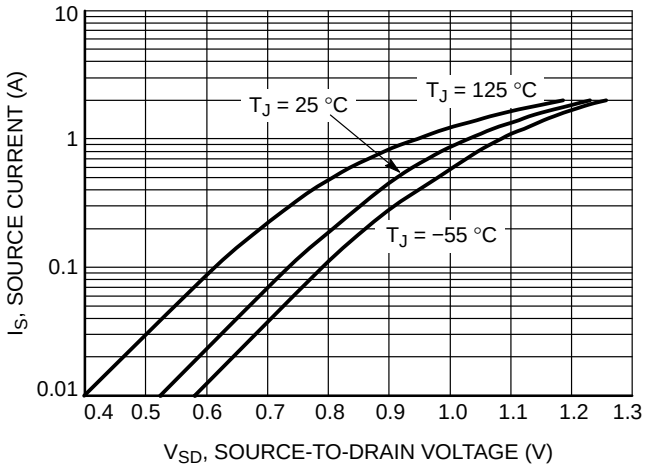


Figure 10. Diode Forward Voltage vs. Current

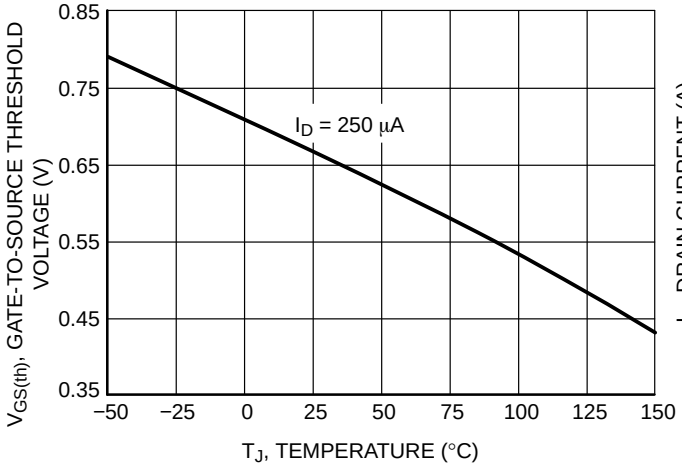


Figure 11. Threshold Voltage

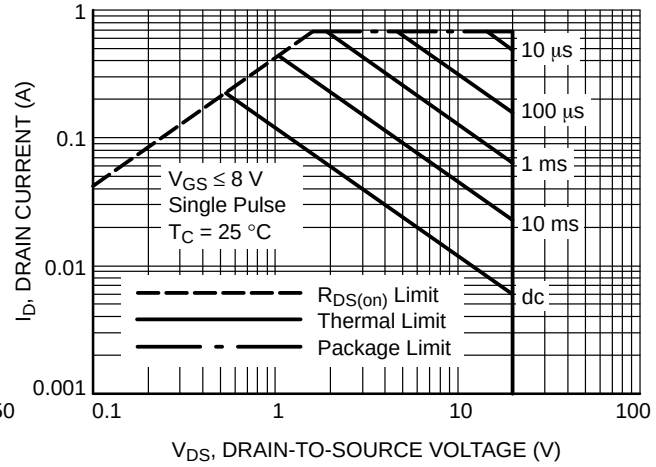


Figure 12. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTICS

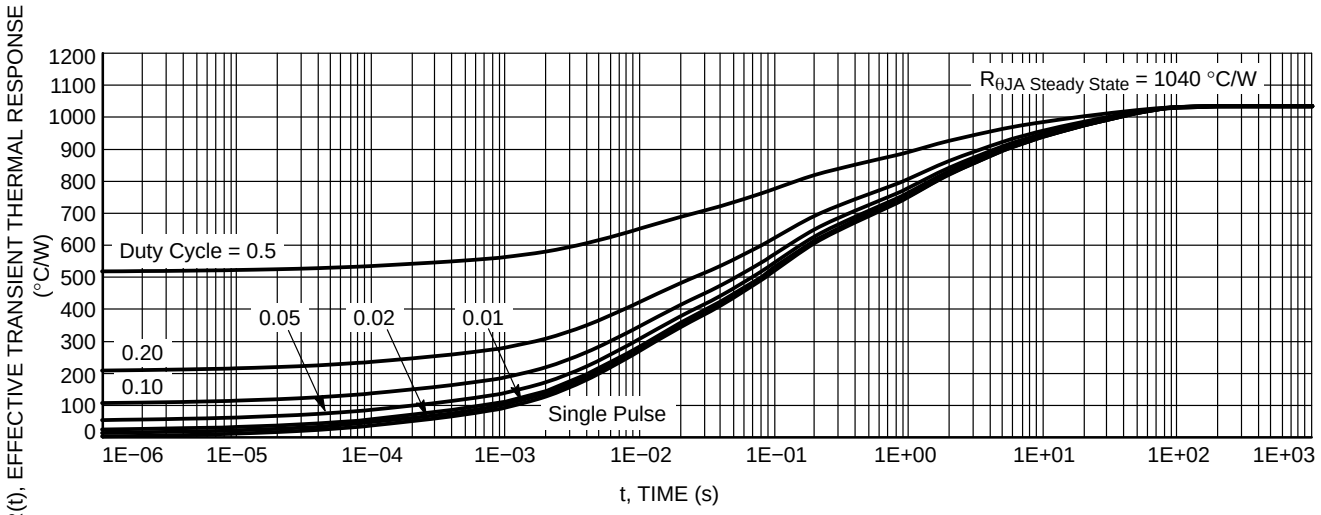
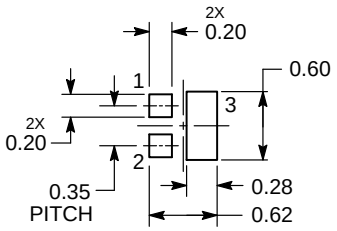


Figure 13. FET Thermal Response

MINIMUM RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

* Dependent upon end user capabilities, this footprint could be used as a minimum.

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REVISION HISTORY

Revision	Description of Changes	Date
2	Rebranded the Data Sheet to **onsemi** format.	11/25/2025

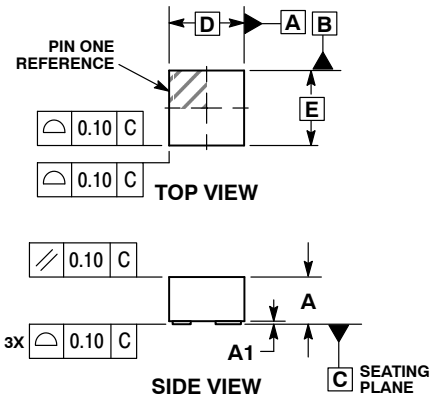
This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

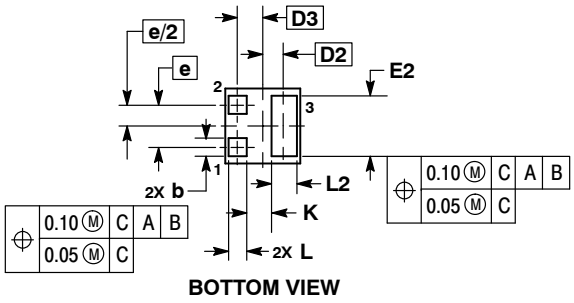
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XLLGA3, 0.62x0.62, 0.35P
CASE 713AB
ISSUE O

SCALE 8:1

DATE 25 SEP 2012





NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.340	0.440
A1	0.000	0.030
b	0.100	0.200
D	0.620 BSC	
D2	0.175 BSC	
D3	0.205 BSC	
E	0.620 BSC	
E2	0.400	0.600
e	0.350 BSC	
K	0.200 REF	
L	0.090	0.210
L2	0.110	0.310

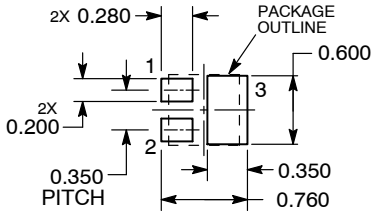
GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G”, may or not be present.

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	**XLLGA3, 0.62X0.62, 0.35P**	**PAGE 1 OF 1**

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